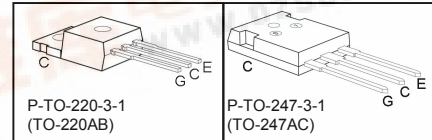
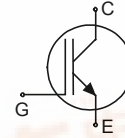




SGP20N60HS SGW20N60HS

High Speed IGBT in NPT-technology

- 30% lower E_{off} compared to previous generation
- Short circuit withstand time – 10 μs
- Designed for operation above 30 kHz
- NPT-Technology for 600V applications offers:
 - parallel switching capability
 - moderate E_{off} increase with temperature
 - very tight parameter distribution
- High ruggedness, temperature stable behaviour
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	E_{off}	T_j	Package	Ordering Code
SGP20N60HS	600V	20	240 μ J	150 $^{\circ}$ C	TO220AB	Q67040-S4498
SGW20N60HS	600V	20	240 μ J	150 $^{\circ}$ C	TO-247AC	Q67040-S4499

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current	I_C	36	A
$T_C = 25^{\circ}$ C		20	
$T_C = 100^{\circ}$ C		20	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	80	
Turn off safe operating area	-	80	
$V_{CE} \leq 600V, T_j \leq 150^{\circ}$ C			
Avalanche energy single pulse $I_C = 20A, V_{CC} = 50V, R_{GE} = 25\Omega$ start $T_j = 25^{\circ}$ C	E_{AS}	115	mJ
Gate-emitter voltage static transient ($t_p < 1\mu s, D < 0.05$)	V_{GE}	± 20 ± 30	V
Short circuit withstand time ¹⁾ $V_{GE} = 15V, V_{CC} \leq 600V, T_j \leq 150^{\circ}$ C	t_{SC}	10	μs
Power dissipation $T_C = 25^{\circ}$ C	P_{tot}	178	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^{\circ}$ C
Time limited operating junction temperature for $t < 150h$	$T_{j(tl)}$	175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	



Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.7	K/W
Thermal resistance, junction – ambient	R_{thJA}	TO-220AB TO-247AC	62 40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=20A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$		2.8 3.5	3.15 4.00	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=500\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	- -	40 2500	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=20A$	-	14		S

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	1100		pF
Output capacitance	C_{oss}		-	105		
Reverse transfer capacitance	C_{riss}		-	64		
Gate charge	Q_{Gate}	$V_{CC}=480V, I_C=20A$ $V_{GE}=15V$	-	100		nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	TO-247AC	-	13		nH
Short circuit collector current ¹⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}\leq 600V,$ $T_j\leq 150^\circ\text{C}$	-	170		A

¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=20\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=16\Omega$ $L_{\sigma}^{1)}$ = 60nH, $C_{\sigma}^{1)}$ = 40pF Energy losses include "tail" and diode reverse recovery.	-	18		ns
Rise time	t_r		-	15		
Turn-off delay time	$t_{d(off)}$		-	207		
Fall time	t_f		-	13		
Turn-on energy	E_{on}		-	0.39		mJ
Turn-off energy	E_{off}		-	0.30		
Total switching energy	E_{ts}		-	0.69		

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$, $I_C=20\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=2.2\Omega$ $L_{\sigma}^{1)}$ = 60nH, $C_{\sigma}^{1)}$ = 40pF Energy losses include "tail" and diode reverse recovery.	-	15		ns
Rise time	t_r		-	8.5		
Turn-off delay time	$t_{d(off)}$		-	65		
Fall time	t_f		-	35		
Turn-on energy	E_{on}		-	0.46		mJ
Turn-off energy	E_{off}		-	0.24		
Total switching energy	E_{ts}		-	0.7		
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$, $I_C=20\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=16\Omega$ $L_{\sigma}^{1)}$ = 60nH, $C_{\sigma}^{1)}$ = 40pF Energy losses include "tail" and diode reverse recovery.	-	17		ns
Rise time	t_r		-	13		
Turn-off delay time	$t_{d(off)}$		-	222		
Fall time	t_f		-	13		
Turn-on energy	E_{on}		-	0.6		mJ
Turn-off energy	E_{off}		-	0.36		
Total switching energy	E_{ts}		-	0.96		

¹⁾ Leakage inductance L_{σ} and Stray capacity C_{σ} due to test circuit in Figure E.

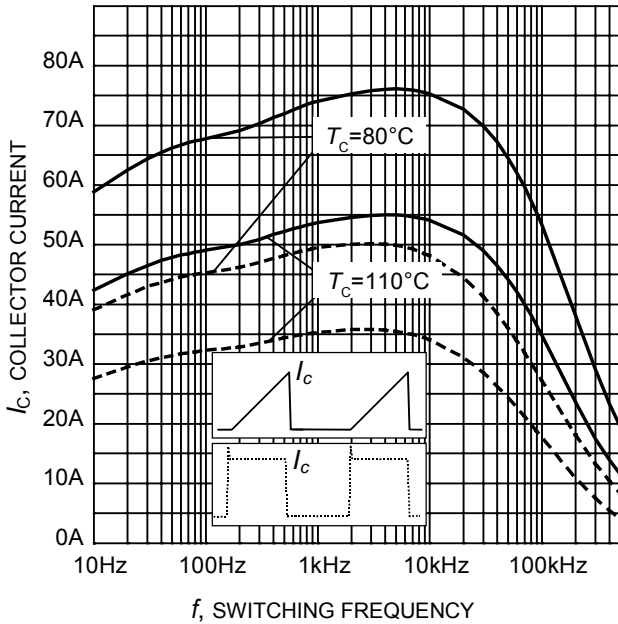


Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/+15\text{V}$, $R_G = 16\Omega$)

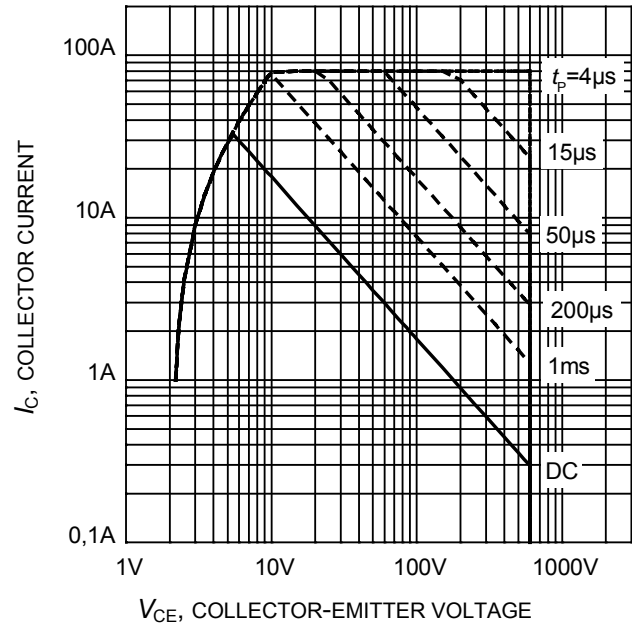


Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$,
 $T_j \leq 150^\circ\text{C}$; $V_{GE} = 15\text{V}$)

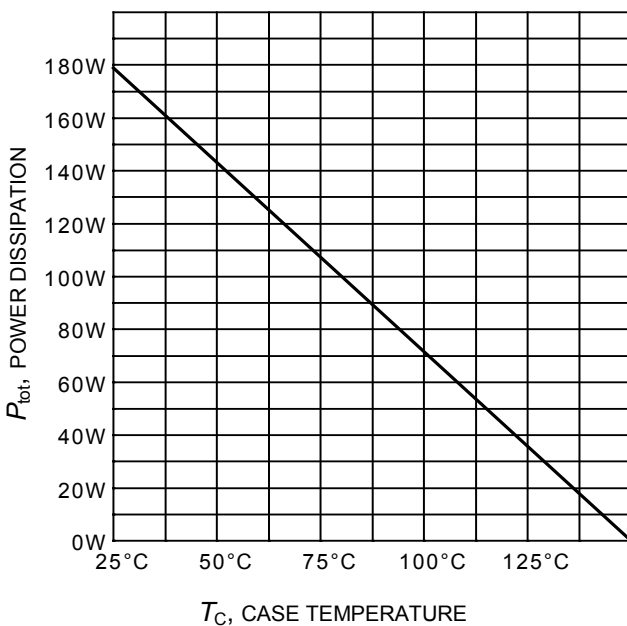


Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 150^\circ\text{C}$)

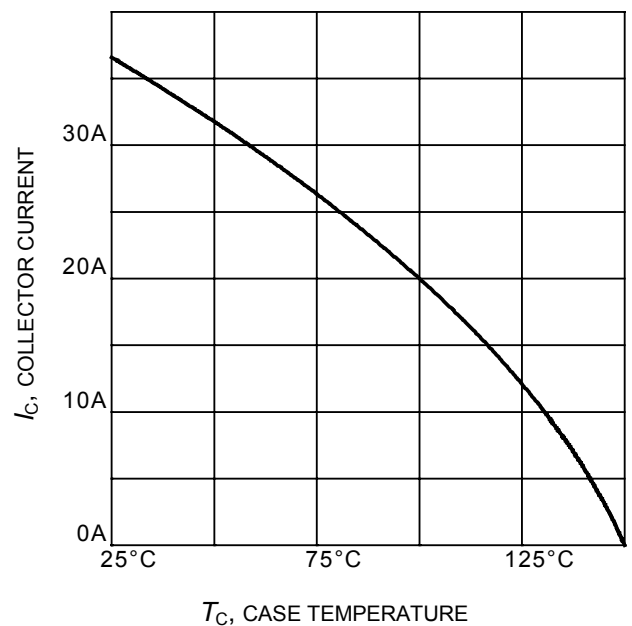


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

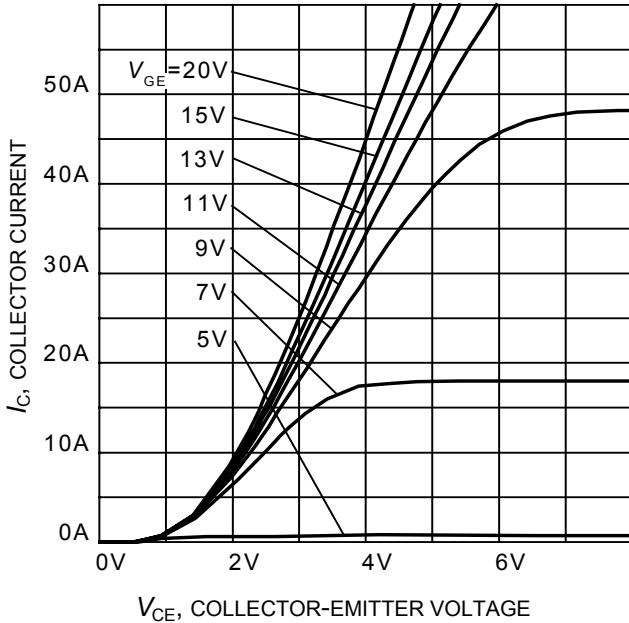


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

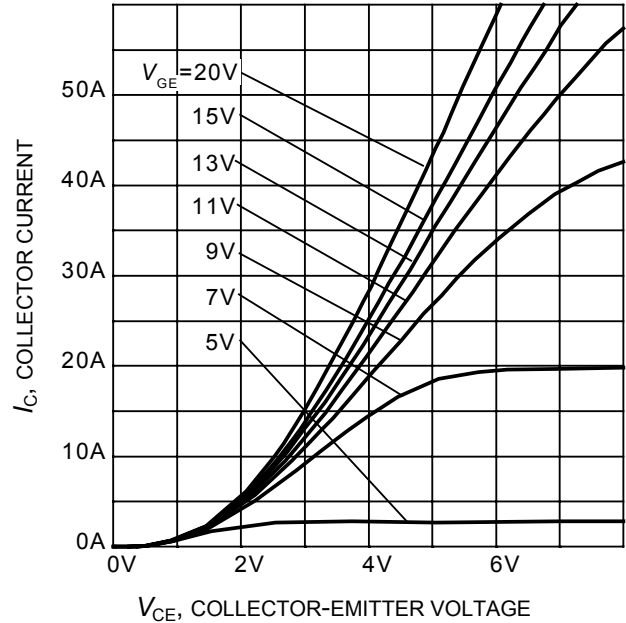


Figure 6. Typical output characteristic
($T_j = 150^\circ\text{C}$)

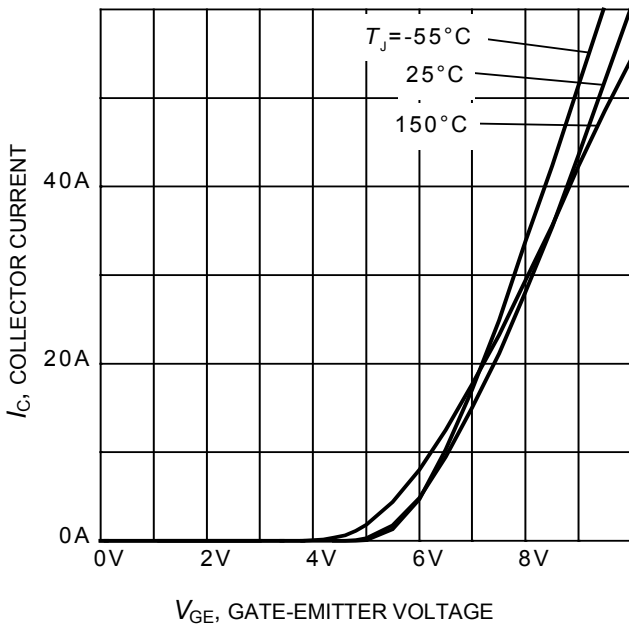


Figure 7. Typical transfer characteristic
($V_{CE} = 10\text{V}$)

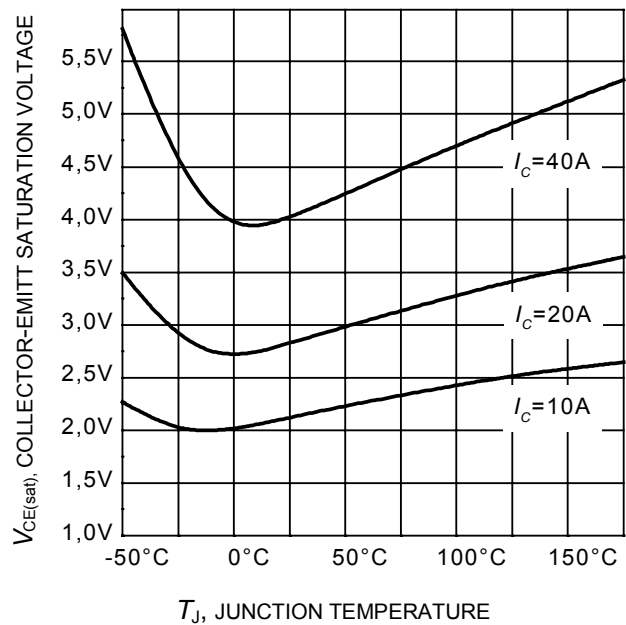


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

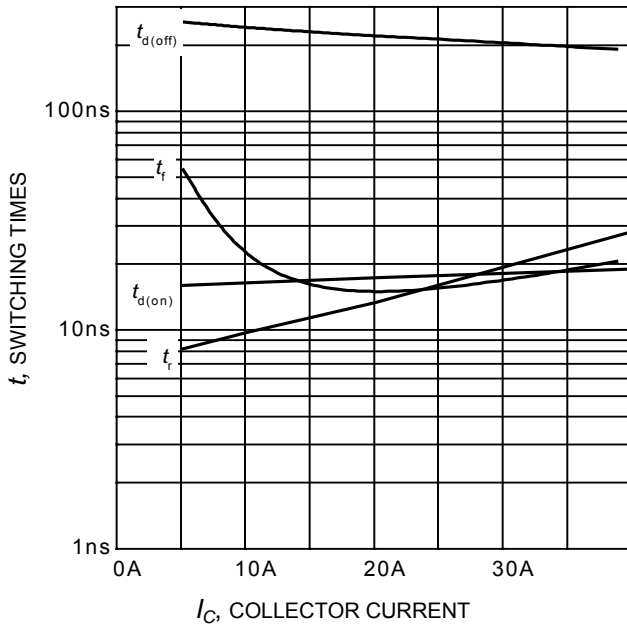


Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_J=150^{\circ}\text{C}$,
 $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=16\Omega$,
 Dynamic test circuit in Figure E)

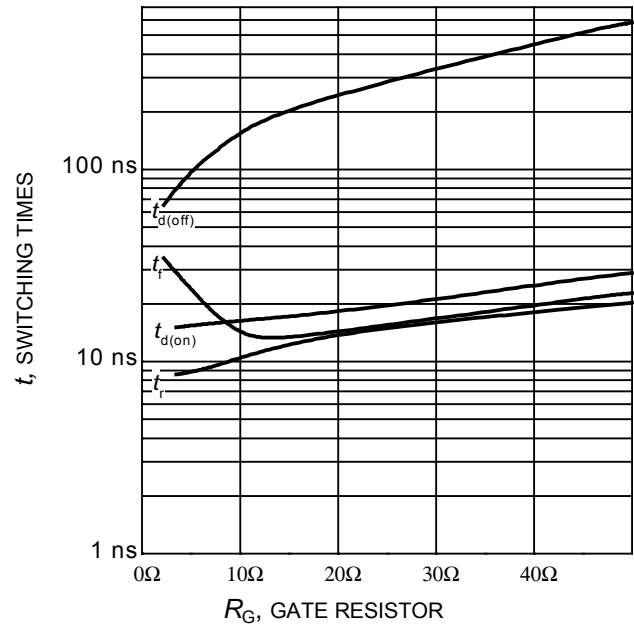


Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_J=150^{\circ}\text{C}$,
 $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=20\text{A}$,
 Dynamic test circuit in Figure E)

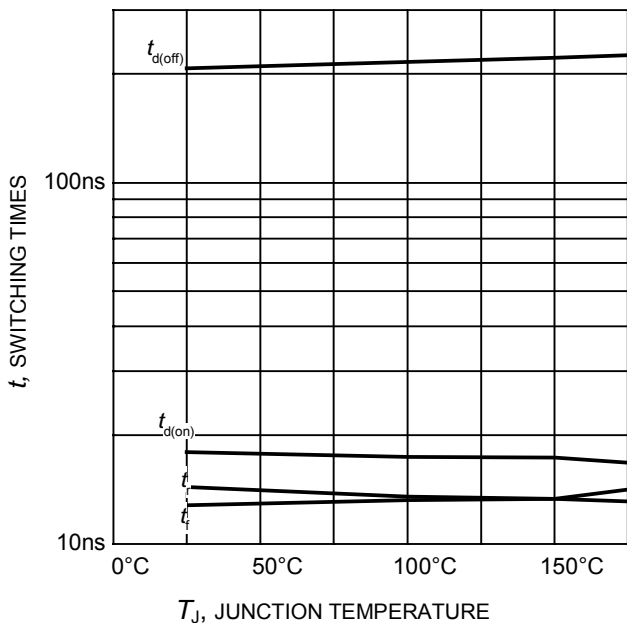


Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE}=400\text{V}$,
 $V_{GE}=0/15\text{V}$, $I_C=20\text{A}$, $R_G=16\Omega$,
 Dynamic test circuit in Figure E)

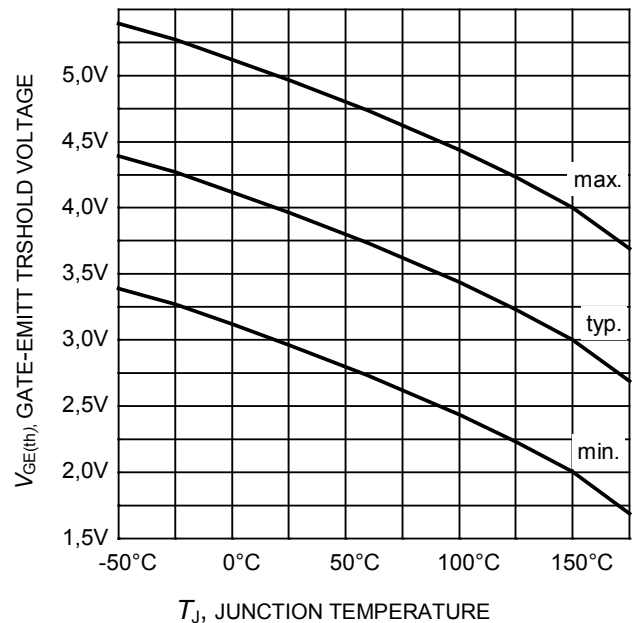


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 0.5\text{mA}$)

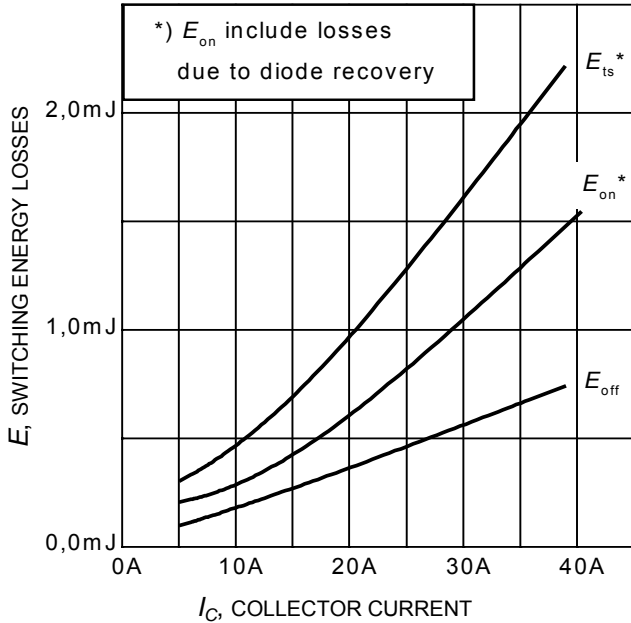


Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_J=150^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=16\Omega$, Dynamic test circuit in Figure E)

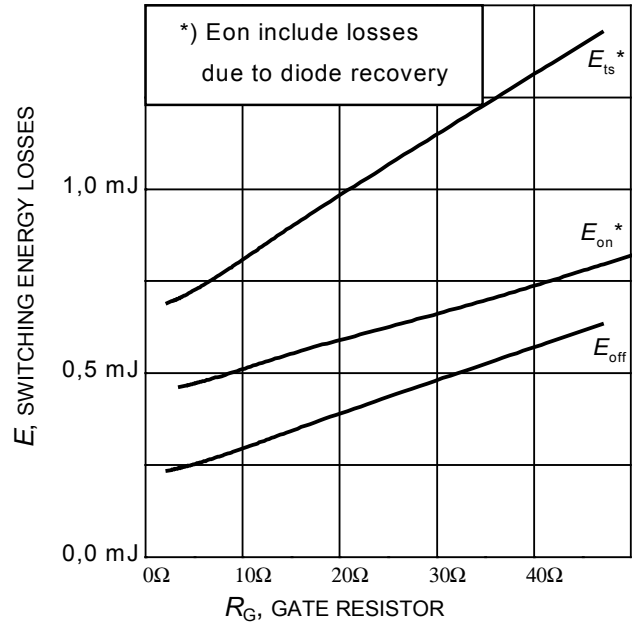


Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_J=150^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=20\text{A}$, Dynamic test circuit in Figure E)

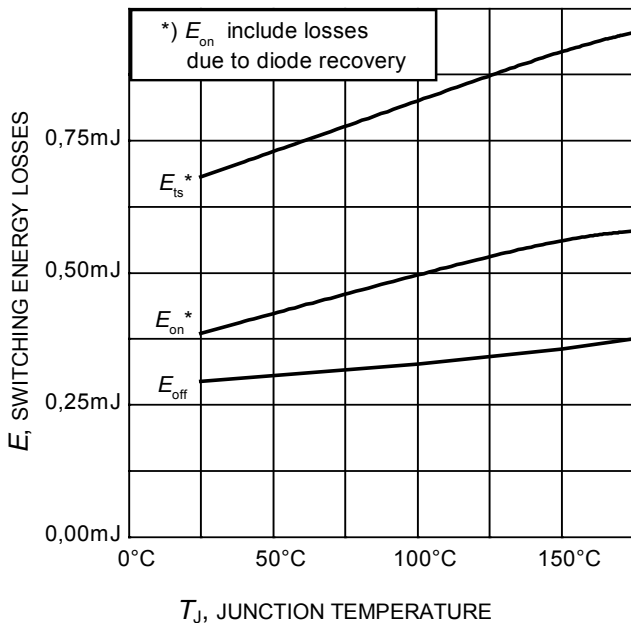


Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=20\text{A}$, $R_G=16\Omega$, Dynamic test circuit in Figure E)

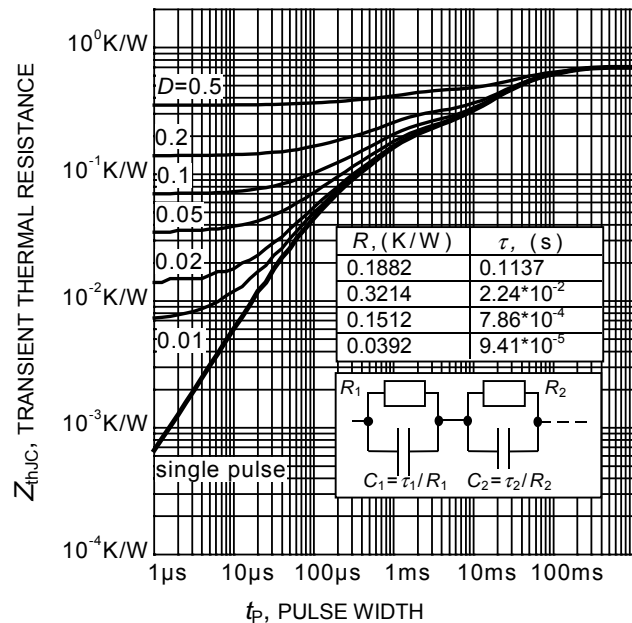


Figure 16. IGBT transient thermal resistance
 ($D = t_p / T$)

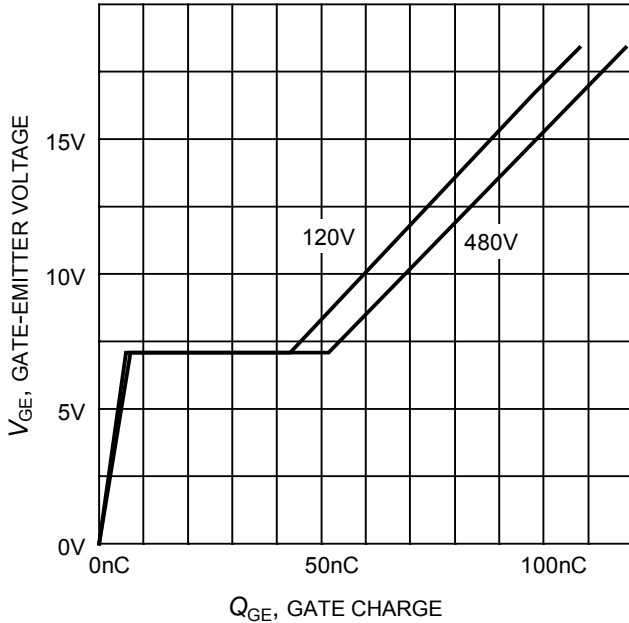


Figure 17. Typical gate charge
($I_C=20\text{ A}$)

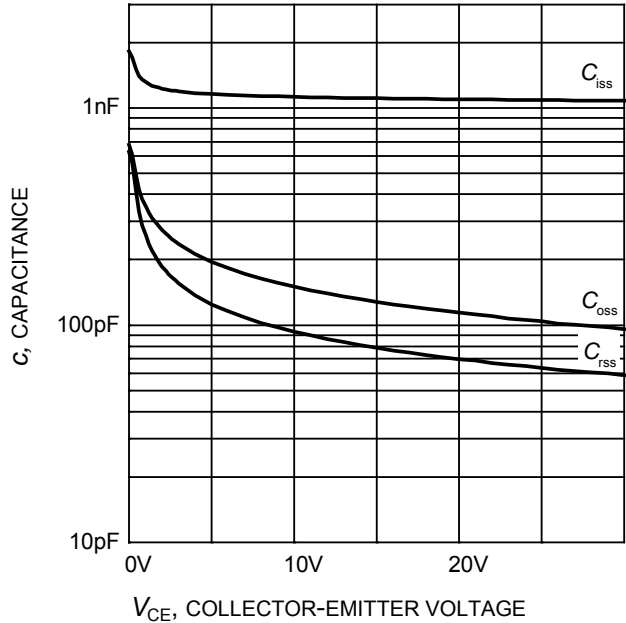


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f = 1\text{ MHz}$)

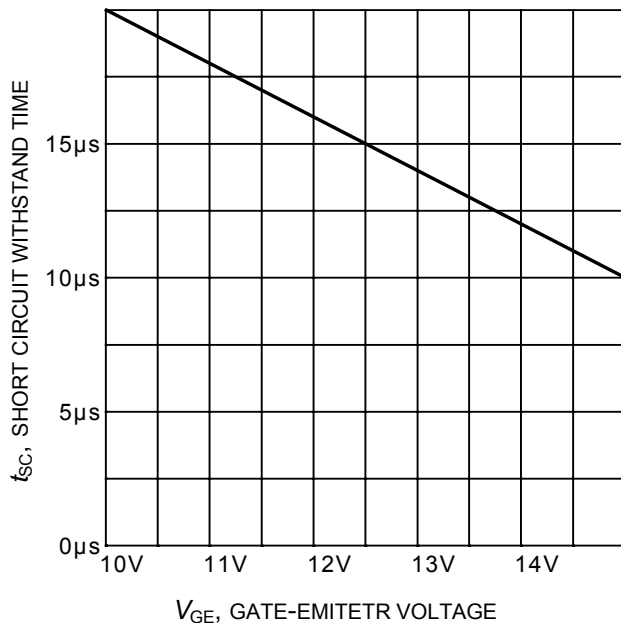


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}=600\text{V}$, start at $T_J=25^\circ\text{C}$)

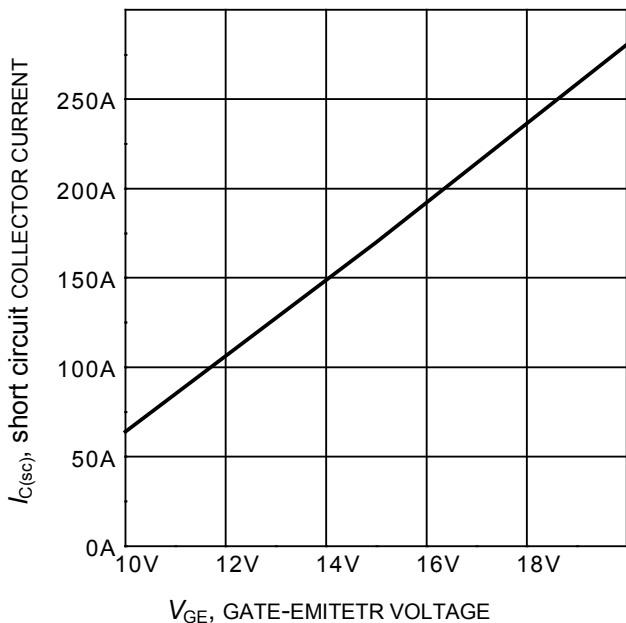
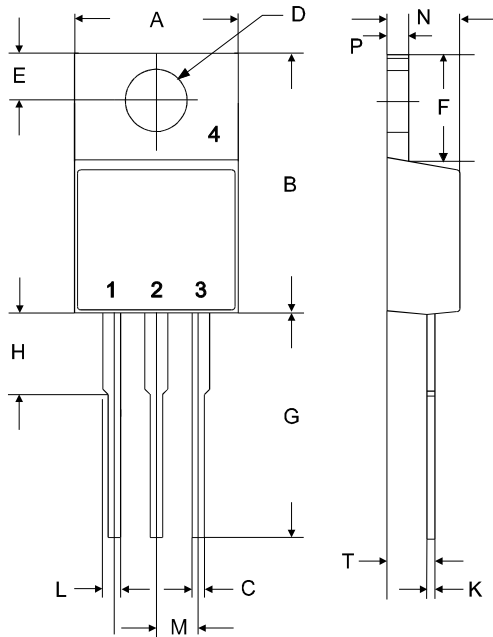


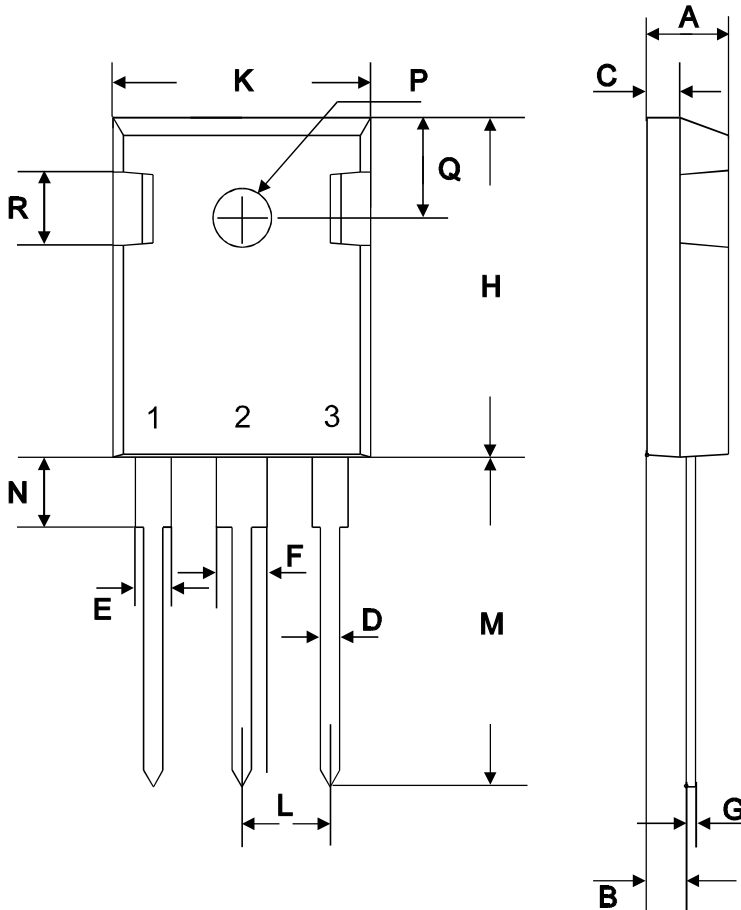
Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600\text{V}$, $T_J \leq 150^\circ\text{C}$)

TO-220AB



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

TO-247AC



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	4.78	5.28	0.1882	0.2079
B	2.29	2.51	0.0902	0.0988
C	1.78	2.29	0.0701	0.0902
D	1.09	1.32	0.0429	0.0520
E	1.73	2.06	0.0681	0.0811
F	2.67	3.18	0.1051	0.1252
G	0.76 max		0.0299 max	
H	20.80	21.16	0.8189	0.8331
K	15.65	16.15	0.6161	0.6358
L	5.21	5.72	0.2051	0.2252
M	19.81	20.68	0.7799	0.8142
N	3.560	4.930	0.1402	0.1941
∅P	3.61		0.1421	
Q	6.12	6.22	0.2409	0.2449

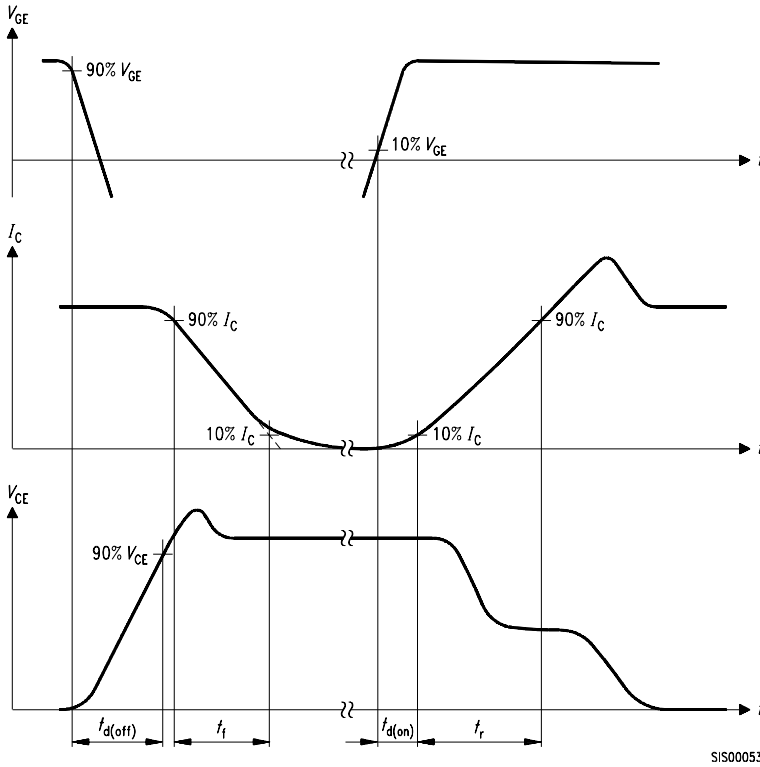


Figure A. Definition of switching times

SIS00053

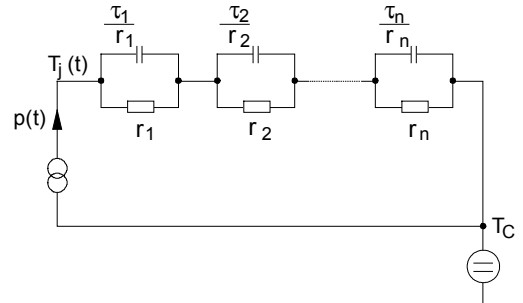


Figure D. Thermal equivalent circuit

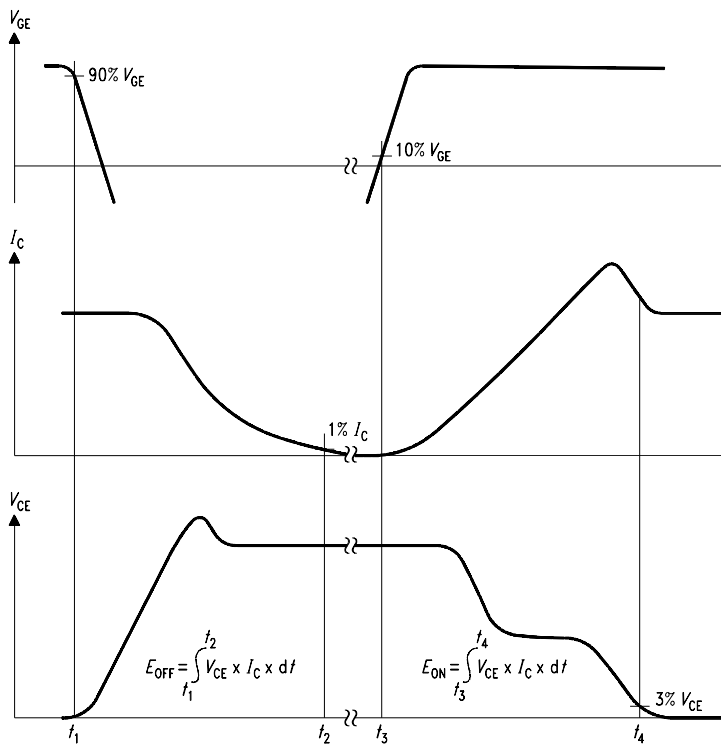


Figure B. Definition of switching losses

SIS

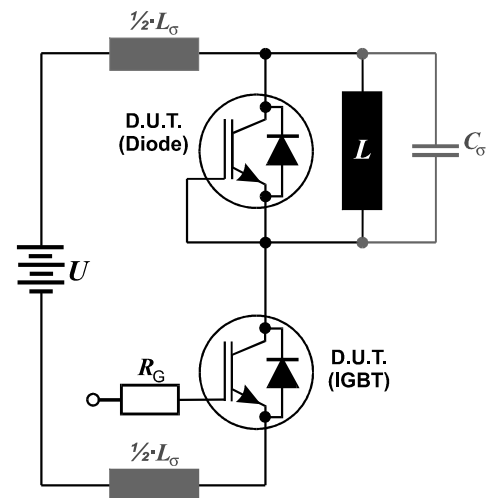


Figure E. Dynamic test circuit
Leakage inductance $L_{\sigma} = 60\text{nH}$
and Stray capacity $C_{\sigma} = 40\text{pF}$.



SGP20N60HS
SGW20N60HS

Bereich Kommunikation
St.-Martin-Strasse 53,
D-81541 München
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